Rochester Electronics

Datasheet

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
    - Class Q Military
    - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

SLDS013B – D2471, DECEMBER 1985 – REVISED MAY 1993

- **Controls 32 Electrodes**
- **100-V Totem-Pole Outputs**
- **Low Standby Power Consumption**
- **All Outputs Contain Sink and Source Clamp Diodes**
- **15-mA Steady-State Output Current**
- **Rugged DMOS Outputs**
- **CMOS Inputs**
- **Direct Replacement for SN55500D and SN75500A**

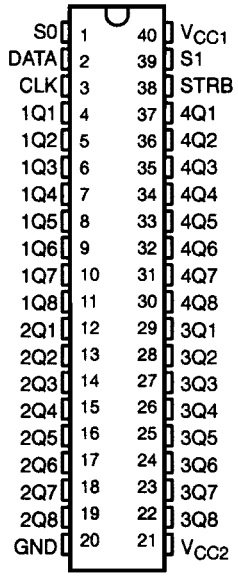
description

The SN55500E, SN65500E, and SN75500E are monolithic BIDFET† integrated circuits designed to perform the line-select operation of a matrix-addressable display. The device inputs are diode-clamped CMOS inputs.

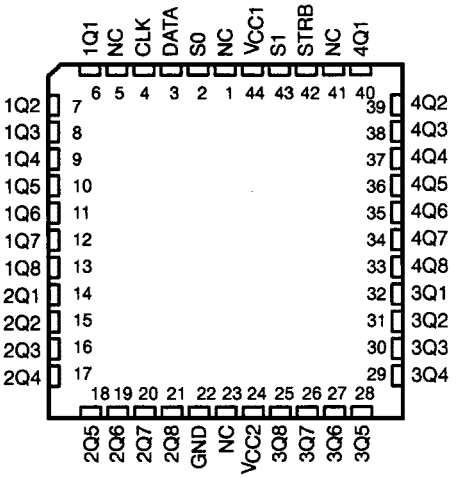
The outputs of these drivers are normally low and can be selectively switched high when the strobe input is low. Selection of the outputs is achieved through the data S0 and S1 inputs. The 8-bit data stored internally in the serial register is inverted and sent to one of four output sections by the 2-line to 4-line decoder. All other outputs remain low. Internal circuits provide a high-current pulse to the level-shifting circuit during positive output transitions. When the output transition is complete, the low steady-state current reduces the circuit's standby power consumption. All outputs contain clamp diodes to the V_{CC2} and GND supply inputs.

The SN55500E is characterized for operation over the full military temperature range of −55°C to 125°C. The SN65500E is characterized for operation from −40°C to 85°C. The SN75500E is characterized for operation from 0°C to 70°C.

SN55500E . . . J PACKAGE
SN65500E, SN75500E . . . N PACKAGE
(TOP VIEW)



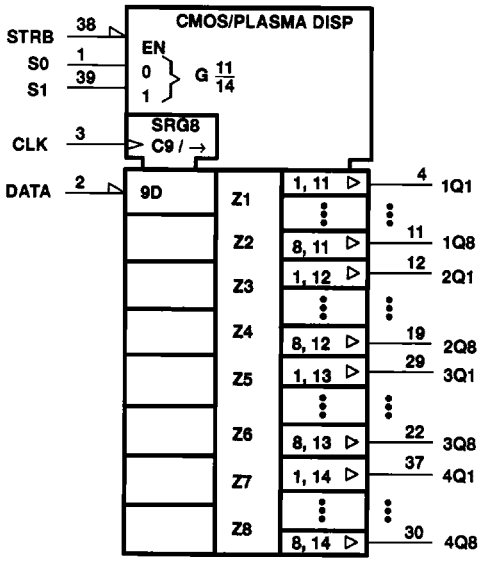
SN55500E . . . FD OR FJ PACKAGE
SN65500E, SN75500E . . . FN PACKAGE
(TOP VIEW)



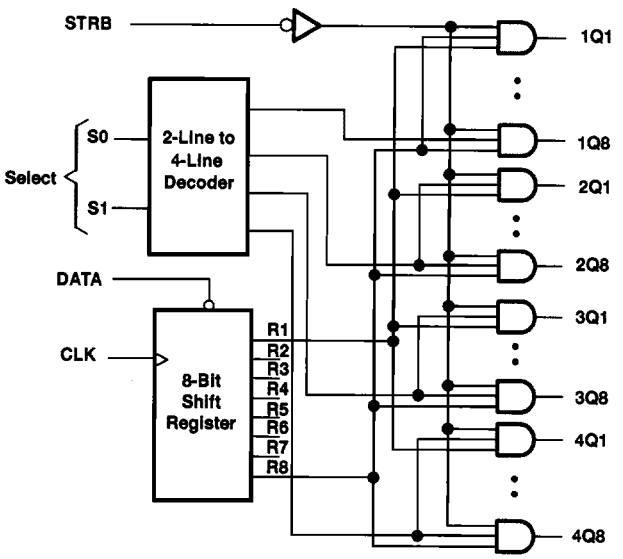
NC – No internal connection

† BIDFET – Bipolar, double-diffused, N-channel and P-channel MOS transistors on same chip. This is a patented process.

logic symbol†



functional block diagram (positive logic)



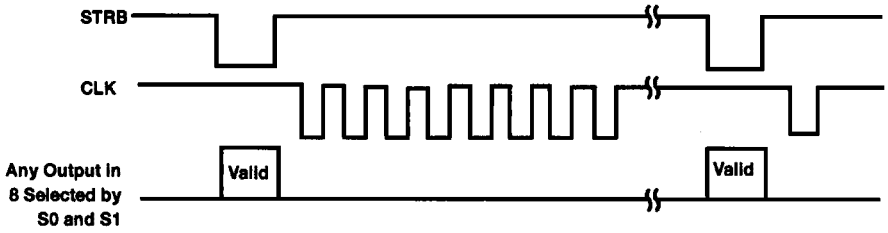
† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the J and N packages.

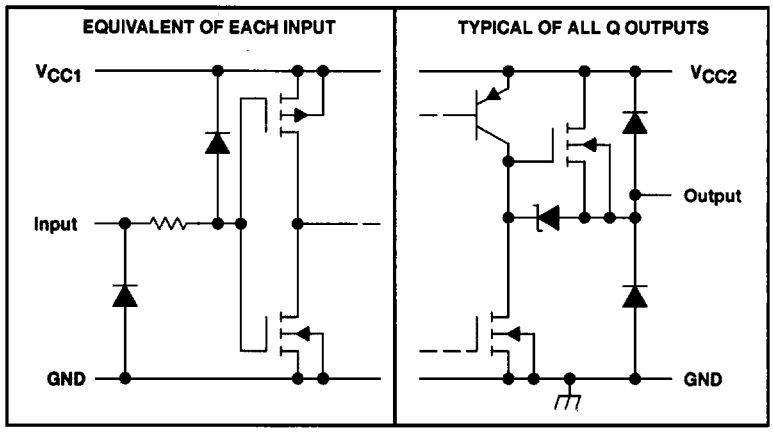
FUNCTION TABLE

FUNCTION	INPUTS					OUTPUTS					
	DATA	CLK	SELECT S1	SELECT S0	STRB	SHIFT REGISTER R1	SHIFT REGISTER R2	SHIFT REGISTER R3 . . . R8	1Q1 . . . 1Q8	2Q1 . . . 2Q8	3Q1 . . . 3Q8	4Q1 . . . 4Q8
Load	H	↑	X	X	H	L	$R1_n$	$R2_n$ . . . $R7_n$	L . . . L	L . . . L	L . . . L	L . . . L
	L	↑	X	X	H	H	$R1_n$	$R2_n$ . . . $R7_n$	L . . . L	L . . . L	L . . . L	L . . . L
Strobe	X	X	X	X	H	$R1_n$	$R2_n$	$R3_n$ . . . $R8_n$	L . . . L	L . . . L	L . . . L	L . . . L
	X	H	L	L	L	$R1_n$	$R2_n$	$R3_n$ . . . $R8_n$	R1 . . . R8	L . . . L	L . . . L	L . . . L
	X	H	L	H	L	$R1_n$	$R2_n$	$R3_n$ . . . $R8_n$	L . . . L	R1 . . . R8	L . . . L	L . . . L
	X	H	H	L	L	$R1_n$	$R2_n$	$R3_n$ . . . $R8_n$	L . . . L	L . . . L	R1 . . . R8	L . . . L
	X	H	H	H	L	$R1_n$	$R2_n$	$R3_n$ . . . $R8_n$	L . . . L	L . . . L	L . . . L	R1 . . . R8

H = high level, L = low level, X = irrelevant, ↑ = low-to-high transition.
R1 . . . R8 = levels currently at internal outputs of shift registers one through eight, respectively.
$R1_n$ . . . $R8_n$ = levels at shift-register outputs R1 through R8, respectively, before the most recent ↑ transition of the clock.

typical operating sequence





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC1} (see Note 1): SN55500E ..... 13.8 V
SN65500E, SN75500E ..... 15 V
Supply voltage, V_{CC2} ..... 100 V
Input voltage ..... V_{CC1} + 0.3 V
Continuous total power dissipation ..... See Dissipation Rating Table
Operating free-air temperature range: SN55500E ..... −55°C to 125°C
SN65500E ..... −40°C to 85°C
SN75500E ..... 0°C to 70°C
Storage temperature range ..... −65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: J package ..... 300°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: N package ..... 260°C
Case temperature for 60 seconds: FD or FJ package ..... 260°C
Case temperature for 10 seconds: FN package ..... 260°C

NOTE 1: Voltage values are with respect to network ground terminal.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 70°C$ POWER RATING	$T_A = 85°C$ POWER RATING	$T_A = 125°C$ POWER RATING
FD or FJ	1825 mW	14.6 mW/°C	1168 mW	949 mW	365 mW
FN	1775 mW	14.2 mW/°C	1136 mW	923 mW	—
J	3050 mW	24.4 mW/°C	1952 mW	1586 mW	610 mW
N	1275 mW	10.2 mW/°C	816 mW	663 mW	—

recommended operating conditions

		SN55500E			SN65500E			SN75500E			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V_{CC1}		10.8	12	13.2	10.8	12	13.2	10.8	12	13.2	V
Supply voltage, V_{CC2}		0		100	0		100	0		100	V
High-level input voltage as a percentage of V_{CC1}, V_{IH}		75%			75%			75%			
Low-level input voltage as a percentage of V_{CC1}, V_{IL}				25%			25%			25%	
High-level output clamp current				20			20			20	mA
Low-level output clamp current				−20			−20			−20	mA
Clock frequency, f_{clock} (see Figure 2)		0		8	0		8	0		8	MHz
Duration of high or low clock pulse, t_w		62			62			62			ns
Setup time, t_{su}	Data inputs before CLK↑	20			20			20			ns
	Select inputs before STRB↓	50			50			50			
Hold time, t_h	Data inputs after CLK↑ (see Note 2)	50			50			50			ns
	Strobe input high after CLK↑	50			50			50			
	Select inputs after STRB↑	50			50			50			
Operating free-air temperature, T_A		−55			−40		85	0		70	°C
Operating case temperature, T_C				125							°C

NOTE 2: For operation above 25°C junction temperature, refer to Figure 2.

electrical characteristics over recommended operating free-air temperature range

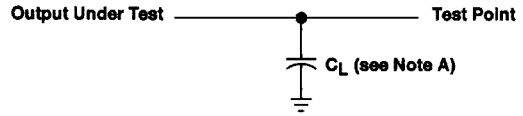
PARAMETER		TEST CONDITIONS		SN55500E			SN65500E			SN75500E			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	Input clamp voltage	V_{CC1} = 12 V,	I_I = −12 mA		−1	−1.5		−1	−1.5		−1	−1.5	V
V_{OH}	High-level output voltage	V_{CC1} = 13.2 V, V_{CC2} = 100 V	I_{OH} = −1 mA	94	97.5		94	97.5		95	97.5		V
			I_{OH} = −10 mA	92	94.5		92	94.5		93	94.5		
			I_{OH} = −15 mA	90	93.5		90	93.5		91	93.5		
V_{OL}	Low-level output voltage	V_{CC1} = 13.2 V, V_{CC2} = 100 V	I_{OL} = 1 mA		0.85	2		0.85	2		0.85	2	V
			I_{OL} = 10 mA		2	4		2	4		2	4	
			I_{OL} = 15 mA		2.75	5		2.75	5		2.75	5	
V_{OK}	Output clamp voltage	V_{CC2} = 0	I_O = 20 mA		1	2.5		1	2.5		1	2.5	V
			I_O = −20 mA		−1.2	−2.5		−1.2	−2.5		−1.2	−2.5	
I_{IH}	High-level input current	V_{CC1} = 13.2 V,	V_I = V_{IH} min			1			1			1	μA
I_{IL}	Low-level input current	V_{CC1} = 13.2 V,	V_I = V_{IL} max			−1			−1			−1	μA
I_{CC1}	Supply current	V_{CC1} = 13.2 V,	V_{CC2} = 100 V		0.05	1		0.05	1		0.05	1	mA
I_{CC2}	Supply current	V_{CC2} = 100 V			1	5		1	5		1	3	mA

† All typical values are at V_{CC1} = 12 V, T_A = 25°C.

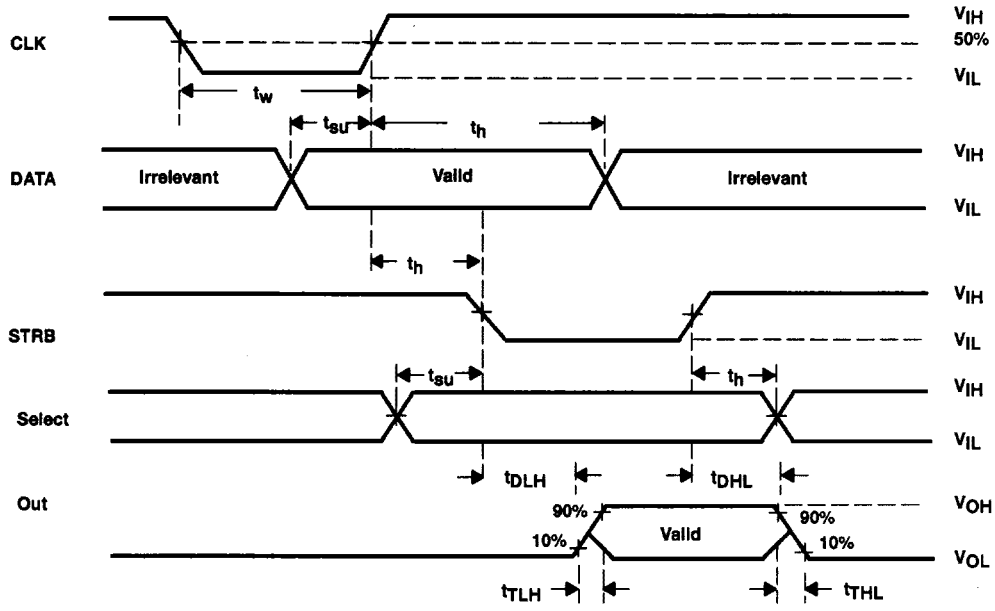
switching characteristics, V_{CC1} = 12 V, V_{CC2} = 100 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
t_{DHL}	Delay time, high-to-low-level output from strobe input	C_L = 30 pF, See Figure 1		250	ns
t_{DLH}	Delay time, low-to-high-level output from strobe input			450	ns
t_{THL}	Transition time, high-to-low-level output			200	ns
t_{TLH}	Transition time, low-to-high-level output			300	ns

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

NOTE A. C_L includes probe and jig capacitance.

Figure 1. Load Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS

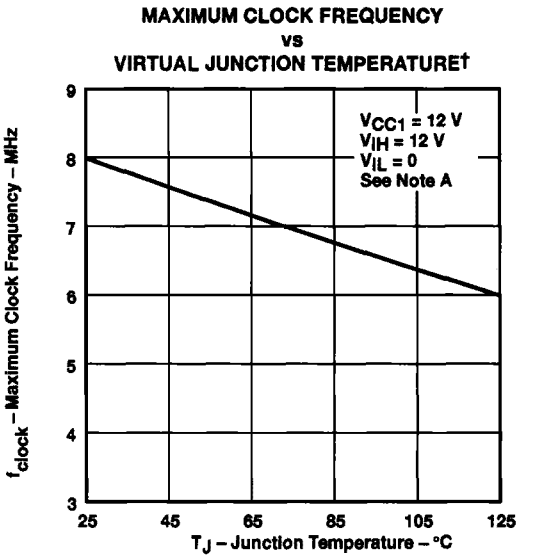


Figure 2

† Only the 25°C to 70°C portion of the curve applies to the SN75500E.
NOTE A: This curve assumes a symmetrical clock pulse.

THERMAL INFORMATION

Junction temperature formula

$$T_J = T_A + P_D R_{\theta JA}$$

$$T_J = T_C + P_D R_{\theta JC}$$

where

T_J = virtual junction temperature
T_A = free-air temperature
P_D = average device power dissipation
R_θ = thermal resistance (junction-to-air, $R_{\theta JA}$, or junction-to-case, $R_{\theta JC}$)

PACKAGE TYPE	$R_{\theta JA}$	$R_{\theta JC}$
FD 44-pin ceramic	68°C/W	20°C/W
FN 44-pin plastic	70°C/W	22°C/W
J 40-pin ceramic	45°C/W	12°C/W
N 40-pin plastic	97°C/W	27°C/W